



1200V FIELD STOP IGBT IN TO-247

Description

The DGTD120T40S1PT is produced using advanced Field Stop Trench IGBT Technology, which provides low $V_{\text{CE}(\text{sat})}$, excellent quality and high switching performance.

Features

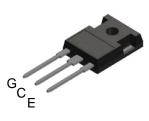
- High-Speed Switching & Low Power Loss
- V_{CE(sat)} = 2.0V @ I_C = 40A
- High Input Impedance
- $t_{rr} = 100 \text{ns (typ)} @ di_F/dt = 200 \text{A/us}$
- Ultra Soft, Fast Recovery Anti-parallel Diode
- Ultra Narrowed VF Distribution Control
- Lead-Free Finish & RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

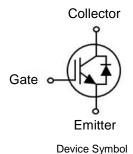
- Motor Drive
- UPS
- Solar Inverter
- IH Cooker

Mechanical Data

- Case: TO-247 (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 5.6 grams (Approximate)



TO-247



Ordering Information (Note 4)

Product	Marking	Quantity		
DGTD120T40S1PT	DGTD120T40S1	450 per Box in Tubes (Note 5)		

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- 5. 30 Devices per Tube

Marking Information



);; = Manufacturer's Marking
DGTD120T40S1 = Product Type Marking Code
YY = Year (ex: 18 = 2018)
LLLLL = Lot Code
WW = Week (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Collector-Emitter Voltage		V _{CE}	1200	V
DC Collector Current	$T_C = 25^{\circ}C$	1	80	Α
DC Collector Current	$T_{C} = 100^{\circ}C$	lc	40	Α
Pulsed Collector Current, tp limited by Tvjmax		I _{CM}	160	Α
Diode Forward Current	$T_C = 25^{\circ}C$	1	80	Α
Diode Forward Current	$T_{C} = 100^{\circ}C$	lF	40	Α
Diode Pulsed Current, tp limited by Tvjmax		I _{FM}	160	Α
Gate-Emitter Voltage		V_{GES}	±20	V
Short Circuit Withstand Time				
$V_{CC} \le 600V$, $V_{GE} = 15V$, $T_{vj} = 150$ °C Allowed Number of Short Circuits < 1000		too	10	μs
		tsc	10	
Time Between Short Circuits ≥ 1.0s				

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	D	357	W
T _C = 100°C	PD	142	VV
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	40	
Thermal Resistance, Junction to Case for IBGT (Note 6)	$R_{ heta JC}$	0.35	°C/W
Thermal Resistance, Junction to Case for Diode (Note 6)	Rejc	0.80	
Operating Temperature	T _{vi}	-55 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board.



Electrical Characteristics (@T_{vj} = +25°C, unless otherwise specified.)

Parameter		Symbol	Min	Тур	Max	Unit	Condition	
STATIC CHARACTERISTICS								
Collector-Emitter Breakdown Voltage		BV _{CES}	1,200	_	_	V	$I_C = 1mA$, $V_{GE} = 0V$	
Collector Emitter Seturation Valtage	T _{vj} = 25°C	.,	-	2.00	2.40	V	I _C = 40A, V _{GE} = 15V	
Collector-Emitter Saturation Voltage	$T_{vj} = 150^{\circ}C$	V _{CE(sat)}	_	2.45	-	V		
Diada Faruard Valtage	T _{vi} = 25°C	.,	-	2.40	3.00	V	I _F = 40A	
Diode Forward Voltage	T _{vj} = 150°C	V _F	_	2.45	-	V		
Gate-Emitter Threshold Voltage		V _{GE(th)}	4.5	5.5	6.5	V	$V_{CE} = V_{GE}$, $I_C = 1mA$	
Zero Gate Voltage Collector Current		I _{CES}	-	-	1.0	mA	V _{CE} = 1200V, V _{GE} = 0V	
Gate-Emitter Leakage Current		I _{GES}	-	-	±250	nA	$V_{GE} = 20V, V_{CE} = 0V$	
DYNAMIC CHARACTERISTICS								
Total Gate Charge		Qg	-	341	-		V 600V I 40A	
Gate-Emitter Charge		Q _{ge}	-	52	-	nC	$V_{CE} = 600V, I_{C} = 40A,$ $V_{GE} = 15V$	
Gate-Collector Charge		Q_{gc}	_	126	-		VGE = 13V	
Input Capacitance		C _{ies}	-	6,030	_		$V_{CE} = 30V$, $V_{GE} = 0V$, $f = 1MHz$	
Reverse Transfer Capacitance		Cres	_	107	_	pF		
Output Capacitance		C _{oes}	_	206	-			
SWITCHING CHARACTERISTICS					,		<u></u>	
Turn-on Delay Time		t _{d(on)}	_	65	-		$V_{GE}=15V,\ V_{CC}=600V,$ $I_{C}=40A,\ R_{G}=10\Omega,$ $Inductive\ Load,$ $T_{vj}=25^{\circ}C$	
Rise time		t _r	-	55	-	ns		
Turn-off Delay Time		t _{d(off)}	-	308	-	110		
Fall Time		t _f	_	40	-			
Turn-on Switching Energy		E _{on}	-	1.96	-			
Turn-off Switching Energy		E _{off}	-	0.54	-	mJ		
Total Switching Energy		E _{ts}	-	2.50	-			
Reverse Recovery Time		t _{rr}	-	100	-	ns	$I_F = 40A$,	
Reverse Recovery Current		I _{rr}	_	7	-	Α	$di_F/dt = 200A/\mu s$,	
Reverse Recovery Charge		Q _{rr}	-	350	-	nC	$T_{vj} = 25^{\circ}C$	
Turn-on Delay Time		t _{d(on)}	_	70	-		V_{GE} = 15V, V_{CC} = 600V, I_C = 40A, R_G = 10 Ω , Inductive Load,	
Rise time		t _r	-	62	-	ns		
Turn-off Delay Time		t _{d(off)}	_	325	-	113		
Fall Time		t _f	_	62	-			
Turn-on Switching Energy		E _{on}	_	2.35	_		T _{vj} = 150°C	
Turn-off Switching Energy		E _{off}	-	1.61	-	mJ	1 vj = 100 0	
Total Switching Energy		E _{ts}	_	3.96	_			
Reverse Recovery Time		t _{rr}	-	180	-	ns	$I_F = 40A$,	
Reverse Recovery Current		Irr	-	10	-	Α	$di_F/dt = 200A/\mu s,$ $T_{vj} = 150^{\circ}C$	
Reverse Recovery Charge		Q _{rr}	-	900	-	nC		



Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.)

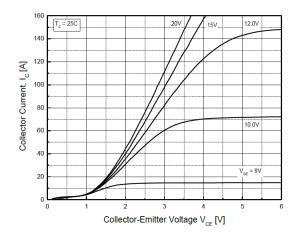


Fig.1 Typical Output Characteristics

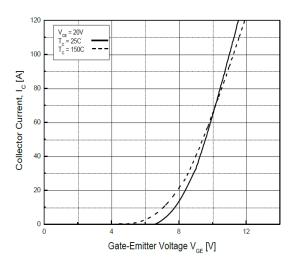


Fig.3 Typical Transfer Characteristics

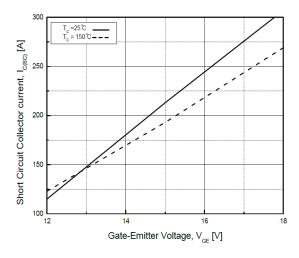


Fig.5 Typical Short Circuit Collector Current

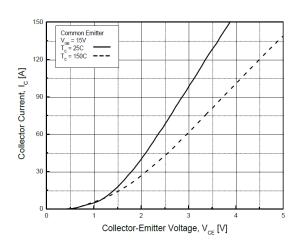


Fig.2 Typical Collector-Emitter Saturation Voltage

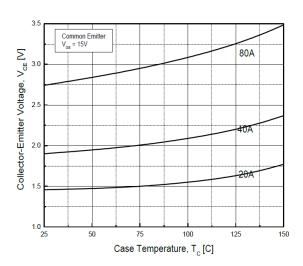


Fig.4 Typical Collector-Emitter Saturation
Voltage at Case Temperature

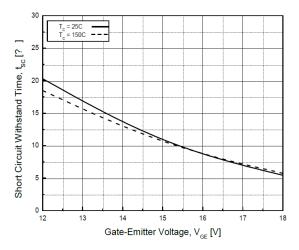


Fig.6 Typical Short Circuit Withstand Time



Typical Performance Characteristics (continued)

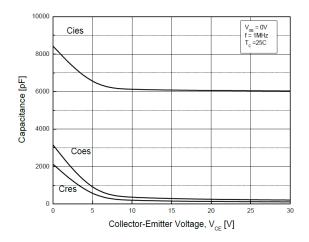


Fig.7 Typical Capacitance

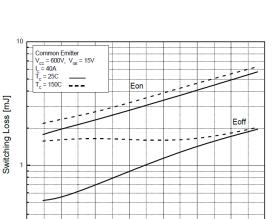


Fig.9 Switching Loss-Gate Resistance

Gate Resistance, $R_{_{\rm G}}$ [ohm]

10

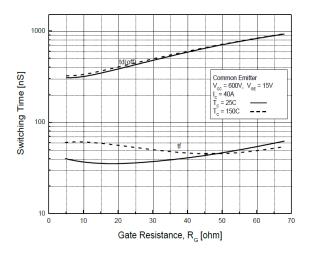


Fig.11 Turn off Characteristics-Gate Resistance

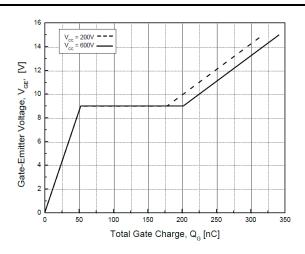


Fig.8 Typical Gate Charge

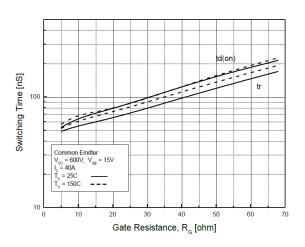


Fig.10 Turn on Characteristics-Gate Resistance

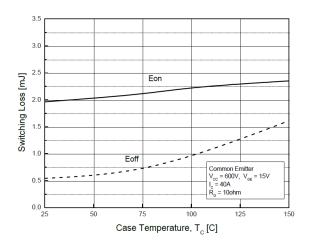


Fig.12 Switching Loss-Case Temperature



Typical Performance Characteristics (cont.)

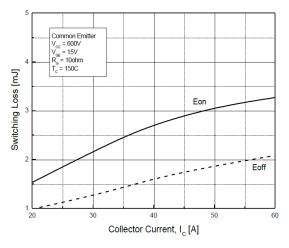


Fig.13 Switching Loss-Collector Current

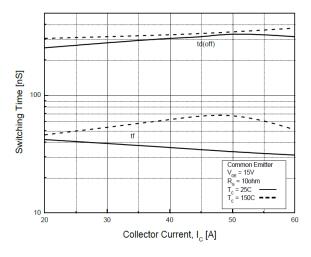


Fig.15 Typical Turn off-Collector Current

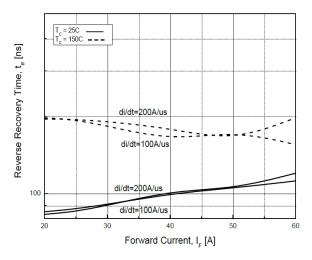


Fig.17 Typical Turn off-Collector Current

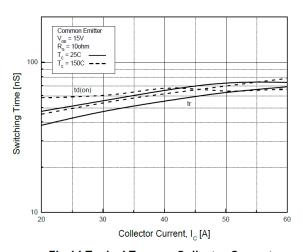


Fig.14 Typical Turn on-Collector Current

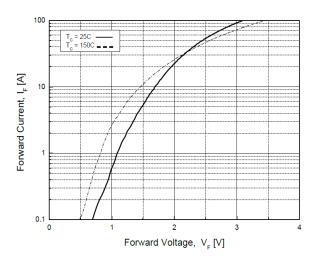


Fig.16 Diode Forward Characteristics

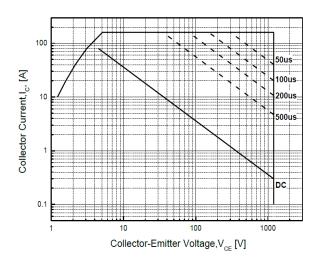
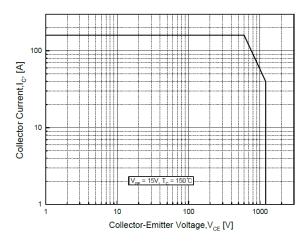


Fig.18 Forward Bias Safe Operating Area



Typical Performance Characteristics (cont.)



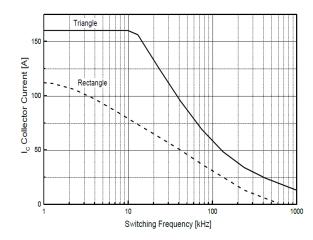


Fig.19 Reverse Bias Safe Operating Area

Fig.20 Switching frequency - Collector current

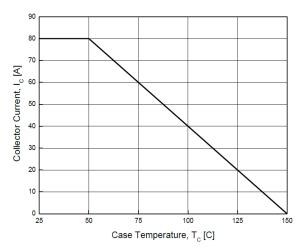


Fig.21 Case Temperature - Collector Current

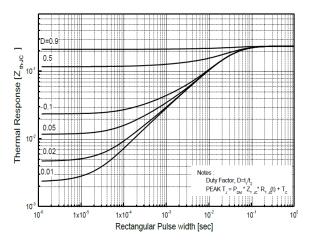


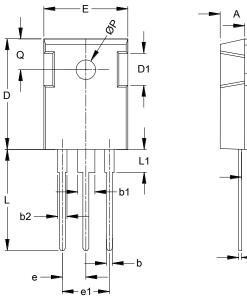
Fig.22 IGBT Transient Thermal Impedance

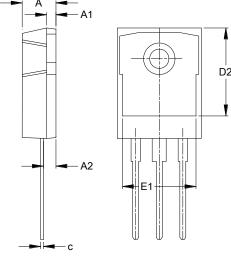


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO-247 (Type MC)





TO-247						
Dim	Min	Тур				
Α	4.700	5.310	-			
A1	1.500	2.490	-			
A2	2.200	2.600	-			
b	0.990	1.400	-			
b1	2.590	-				
b2	1.650	2.390	-			
С	0.380	0.890	-			
D	20.30	21.46	-			
D1	4.320	5.490	-			
D2	13.08	-	-			
Е	15.45	16.26	-			
E1	13.06	-				
е	5.450					
e1	10.90					
L	19.81	20.57	-			
L1	-	4.500	-			
ø	5.380	6.200	-			
øΡ	3.500 3.700 -					
All Dimensions in mm						

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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